

App. Serial No. 10/560,573
Docket No.: US030162US2

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In the Abstract:

Please amend the abstract as indicated below.

A Silicon on Insulator device is disclosed wherein a parasitic channel (~~110~~) induced in a thin film portion of the device is prevented from allowing current flow between the source (~~101~~) and drain (~~101~~) by a Deep N implant directly below the source or drain. The deep N implant prevents a depletion region from being formed, thereby cutting off current flow between the source (~~101~~) and the drain (~~101~~) that would otherwise occur.

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A Silicon on Insulator device is disclosed wherein a parasitic channel induced in a thin film portion of the device is prevented from allowing current flow between the source and drain by a Deep N implant directly below the source or drain. The deep N implant prevents a depletion region from being formed, thereby cutting off current flow between the source and the drain that would otherwise occur.